TOSHIBA Intelligent Power Device Silicon Monolithic Power MOS IC

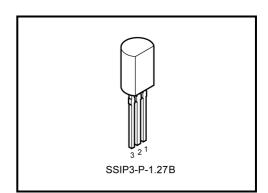
TPD1028BS

Low-Side Switch for Motors, Solenoids, and Lamp Drivers

TPD1028BS is a monolithic power IC for low-side switch. The IC has a vertical MOSFET output which can be directly driven from a CMOS or TTL logic circuit (e.g., an MPU). The IC offers intelligent self-protection functions.

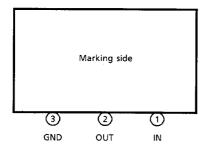
Features

- A monolithic power IC with a new structure combining a control block and a vertical power MOSFET (π -MOS) on a single chip.
- Can directly drive a power load from a CMOS or TTL logic.
- Built-in Protection circuits against overvoltage, load short circuiting, and thermal shutdown.
- Low on-resistance. RDS (ON) = 0.25 (max) (@VIN = 5 V, T_j = 25°C)
- Package TO-92(MOD) can be packed in tape.



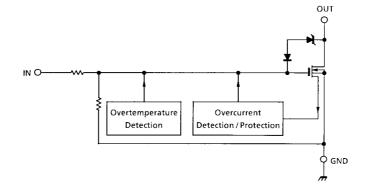
Weight: 0.36 g (typ.)

Pin Assignment



Note: That because of its MOS structure, this product is sensitive to static electricity.

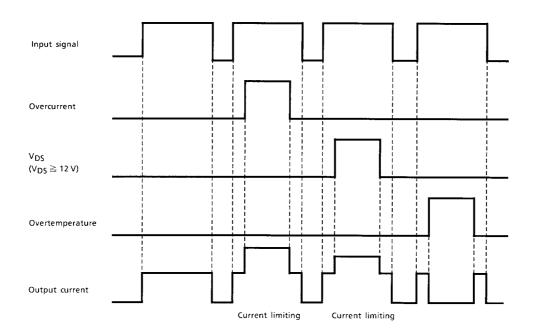
Block Diagram



Pin Description

Pin No.	Symbol	Pin Description
1	IN	Input pin. This pin is connected to a pull-down resistor internally, so that even when input wiring is open-circuited, outputcan never be turned on inadvertently.
2	OUT	Output pin. If an inrush current flows (e.g., from a lamp), the current is clamped at 10 A (typ.) by an overcurrent protective circuit. Also, a 150 µs (typ.) mask circuit is included internally, so that if V _{DS} ≥12 V (typ.) after this mask time, the current is clamped at 3 A (typ.).
3	GND	Ground pin.

Timing Chart



Truth Table

In	Vout	State		
L	Н	Normal		
Н	L	Normai		
L	н	Overcurrent		
н	L	(during inrush)		
L	н	Overcurrent		
н	L	(shorted load)		
L	н	Overtemporature		
Н	Н	Overtemperature		

Maximum Rating (Ta = 25°C)

Characteristic	Symbol	Rating	Unit	
Drain-source voltage	V _{DS (DC)}	40	V	
Output current	I _D	1.5	А	
Input voltage	V _{IN}	- 0.5 ~ 6	V	
Power dissipation	PD	0.9	W	
Energy tolerance	E _{S/B}	200	mJ	
Operating temperature	T _{opr}	- 40 ~ 85	°C	
Junction temperature	Tj	150	°C	

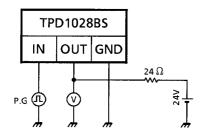
Electrical Characteristics ($T_j = 25^{\circ}C$)

Characteristic	Symbol	Test Cir- cuit	Test Condition	Min	Тур.	Max	Unit
Drain-source breakdown voltage	V (BR) DSS	_	V _{IN} = 0 V, I _D = 10 mA	40	_	_	V
Operating supply voltage	V _{DD}	—	—	_	_	38	V
	V _{IH(1)}	-	V _{DS} = 24 V, I _D = 1 A	4.5	5	5.5	v
High level input voltage	V _{IH(2)}	_	V _{DS} = 10 V, I _D = 0.75 A	3.9	5	5.7	
	V _{IH(3)}	_	V _{DS} = 38 V, I _D = 0.75 A	3.9	5	5.7	
	V _{IL(1)}	_	V _{DS} = 24 V, I _D = 10 μA	—	_	0.8	V
Low level input voltage	V _{IL(2)}	-	V _{DS} = 10 V, I _D = 10 μA	_	-	0.8	
	V _{IL(3)}	-	V _{DS} = 38 V, I _D = 10 μA	_	-	0.8	
Current at output off	I _{DSS(1)}		V _{IN} = 0 V, V _{DS} = 40 V	—	_	100	μA
	I _{DSS(2)}		V _{IN} = 0 V, V _{DS} = 24 V	—	_	10	
Input current	I _{IN}	_	V _{IN} = 5 V, at normal operation	-	_	300	μA
On resistance	R _{DS(ON)}	_	V _{IN} = 5 V, I _D = 1 A	_	_	0.25	Ω
Thermal shutdown temperature	Τ _S	—	V _{IN} = 5 V	_	160	_	°C
Overcurrent protection	I _{S(1)}	_	V _{DS} = 24 V, V _{IN} = 5 V, during inrush	_	10	_	A
	I _{S(2)}	_	V_{DS} = 24 V, V_{IN} = 5 V, when shorted load	_	3	_	
Shorted load detection voltage	V _{DS}	_	when shorted load	_	12	_	V
Switching time	t _{ON} 1	1	$V_{\text{DS}} = 24 \text{ V}, \text{ V}_{\text{IN}} = 5 \text{ V},$ R _L = 24 Ω	_	70	_	μs
	tOFF				120	_	
Diode forward voltage between drain and source	V _{DSF}	_	I _F = 1.5 A	_	0.9	1.8	V

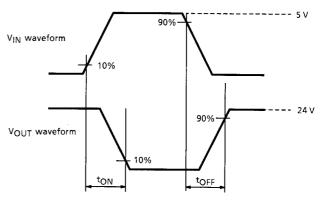
Test Circuit 1

Switching time measuring circuit

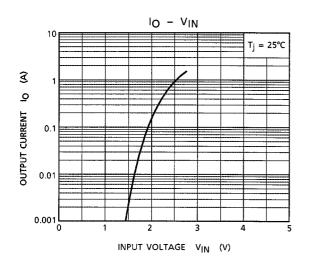
Test circuit

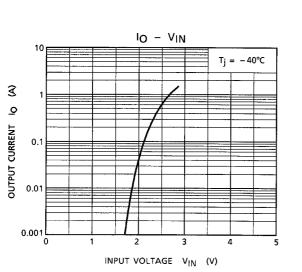


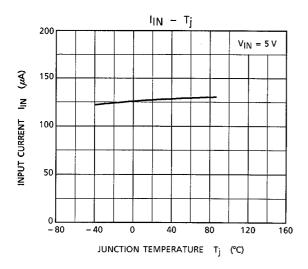
Measured waveforms

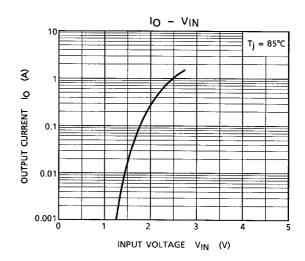


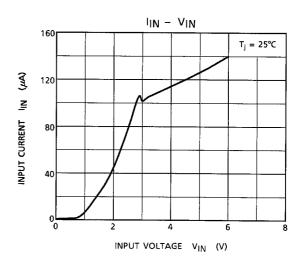
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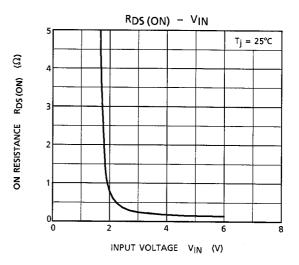




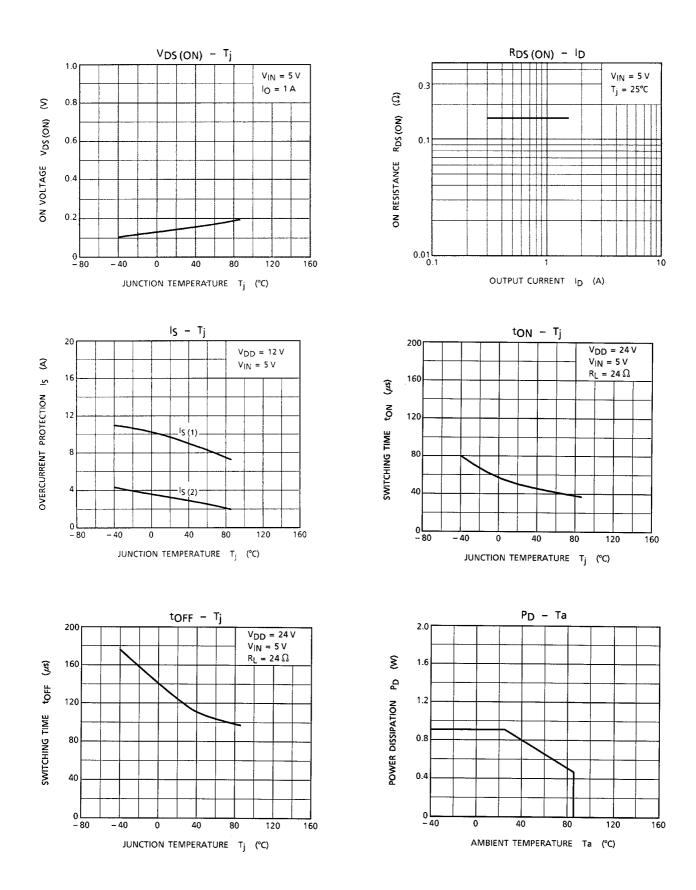








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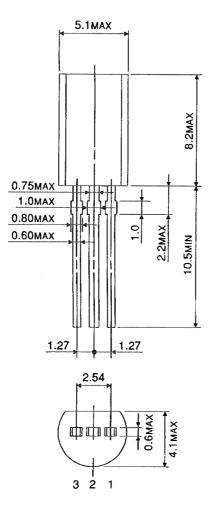
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TPD1028BS

Package Dimensions

SSIP3-P-1.27B

Unit : mm



Weight: 0.36 g (typ.)

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